

主要参数 MAIN CHARACTERISTICS

ID	80 A
VDSS	100 V
Rdson-typ (@Vgs=10V)	7.5 mΩ
Rdson-typ (@Vgs=4.5V)	10.5 mΩ
Qg-typ	54 nC

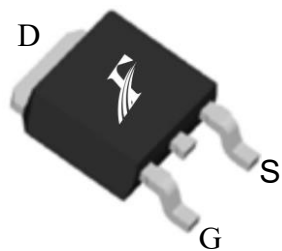
用途 APPLICATIONS

开关电源	Switching Power Supply
同步整流	Synchronous Rectification

产品特性 FEATURES

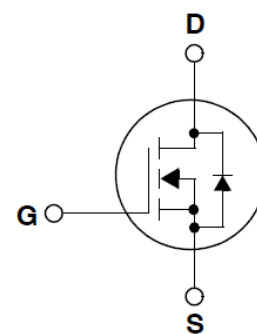
低栅极电荷	Low gate charge
低 Crss (典型值 12 pF)	Low Crss (typical 12 pF)
开关速度快	Fast switching
100%经过雪崩测试	100% avalanche tested
100%经过热阻测试	100% DVDS tested
100%经过 Rg 测试	100% Rg tested
高抗 dv/dt 能力	Improved dv/dt capability
符合 RoHS 标准	ROHS compliant
SGT 工艺	SGT technology

封装形式 Package



TO-252
FHD series

等效电路 Equivalent Circuit



绝对最大额定值 ABSOLUTE RATINGS (Tc25°C)

项目 Parameter	符号 Symbol	数值 Value	单位 Unit
最高漏极-源极直流电压 Drain-Source Voltage	V _{DS}	100	V
连续漏极电流* Drain Current -continuous *	I _D (T _c =25°C)	80	A
	I _D (T _c =100°C)	63	A
最大脉冲漏极电流 (注 1) Drain Current – pulse (note 1)	I _{DM}	340	A
最高栅源电压 Gate-Source Voltage	V _{GS}	±20	V
单脉冲雪崩能量 (注 2) Single Pulsed Avalanche Energy (note 2)	E _{AS}	156	mJ
雪崩电流 (注 1) Avalanche Current (note 1)	I _{AS}	25	A
二极管反向恢复最大电压变化速率 (注 3) Peak Diode Recovery dv/dt (note 3)	dv/dt	5.0	V/ns
耗散功率 Power Dissipation	P _D (TC=25°C)	85	W
	-Derate above 25°C	0.68	W/°C
最高结温及存储温度 Operating and Storage Temperature Range	T _J , T _{STG}	150,-55~+150	°C
引线最高焊接温度 Maximum Lead Temperature for Soldering Purposes	T _L	260	°C

*漏极电流由最高结温限制

*Drain current limited by maximum junction temperature

电特性 ELECTRICAL CHARACTERISTICS

项目 Parameter	符号 Symbol	测试条件 Tests conditions	最小 Min	典型 Typ	最大 Max	单位 Units
关态特性 Off –Characteristics						
漏-源击穿电压 Drain-Source Voltage	BV _{DSS}	I _D =250μA, V _{GS} =0V	100	-	-	V
击穿电压温度特性 Breakdown Voltage Temperature Coefficient	ΔBV _{DSS} /ΔT _J	I _D =250μA, referenced to 25°C	-	0.1	-	V/°C
零栅压下漏极漏电流 Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =100V, V _{GS} =0V, T _C =25°C	-	-	1	μA
		V _{DS} =80V, T _C =125°C	-	-	100	μA
栅极体漏电流 Gate-body leakage current	I _{GSS} (F/R)	V _{DS} =0V, V _{GS} =±30V	-	-	±100	nA
通态特性 On-Characteristics						
阈值电压 Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D =250μA	1.0	1.8	2.5	V
静态导通电阻 Static Drain-Source On-Resistance	R _{DS(ON)}	V _{GS} =10V , I _D =40A	-	7.5	8.0	mΩ
		V _{GS} =4.5V , I _D =40A	-	10.5	12	mΩ
动态特性 Dynamic Characteristics						
栅电阻 Gate Resistance	R _g	f=1.0MHz, V _{DS} OPEN	-	1.0	-	Ω
输入电容 Input capacitance	C _{iss}	V _{DS} =50V, V _{GS} =0V, f=1.0MHz	-	2700	-	pF
输出电容 Output capacitance	C _{oss}		-	768	-	
反向传输电容 Reverse transfer capacitance	C _{rss}		-	12	-	
开关特性 Switching Characteristics						
延迟时间 Turn-On delay time	t _{d(on)}	V _{DS} =50V, I _D =40A, R _G =3Ω V _{GS} =10V (note 4, 5)	-	19	-	ns
上升时间 Turn-On rise time	t _r		-	27	-	ns
延迟时间 Turn-Off delay time	t _{d(off)}		-	35	-	ns
下降时间 Turn-Off Fall time	t _f		-	21	-	ns
栅极电荷总量 Total Gate Charge	Q _g	V _{DS} =50V , I _D =40A , V _{GS} =10V (note 4, 5)	-	54	-	nC
栅-源电荷 Gate-Source charge	Q _{gs}		-	10.5	-	nC
栅-漏电荷 Gate-Drain charge	Q _{gd}		-	11	-	nC
漏-源二极管特性及最大额定值 Drain-Source Diode Characteristics and Maximum Ratings						
正向最大连续电流 Maximum Continuous Drain-Source Diode Forward Current		I _S	-	-	80	A
正向最大脉冲电流 Maximum Pulsed Drain-Source Diode Forward Current		I _{SM}	-	-	320	A
正向压降 Drain-Source Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _S =40A	-	-	1.2	V
反向恢复时间 Reverse recovery time	t _{rr}	V _{GS} =0V, I _S =40A ,dI _F /dt=100A/μs (note 4)	-	58	-	ns
反向恢复电荷 Reverse recovery charge	Q _{rr}		-	103	-	nC

热特性 THERMAL CHARACTERISTIC

项目 Parameter	符号 Symbol	FHD80N1F7LA	单位 Unit
结到管壳的热阻 Thermal Resistance, Junction to Case	Rth(j-c)	1.47	°C/W
结到环境的热阻 Thermal Resistance, Junction to Ambient	Rth(j-A)	60	°C/W

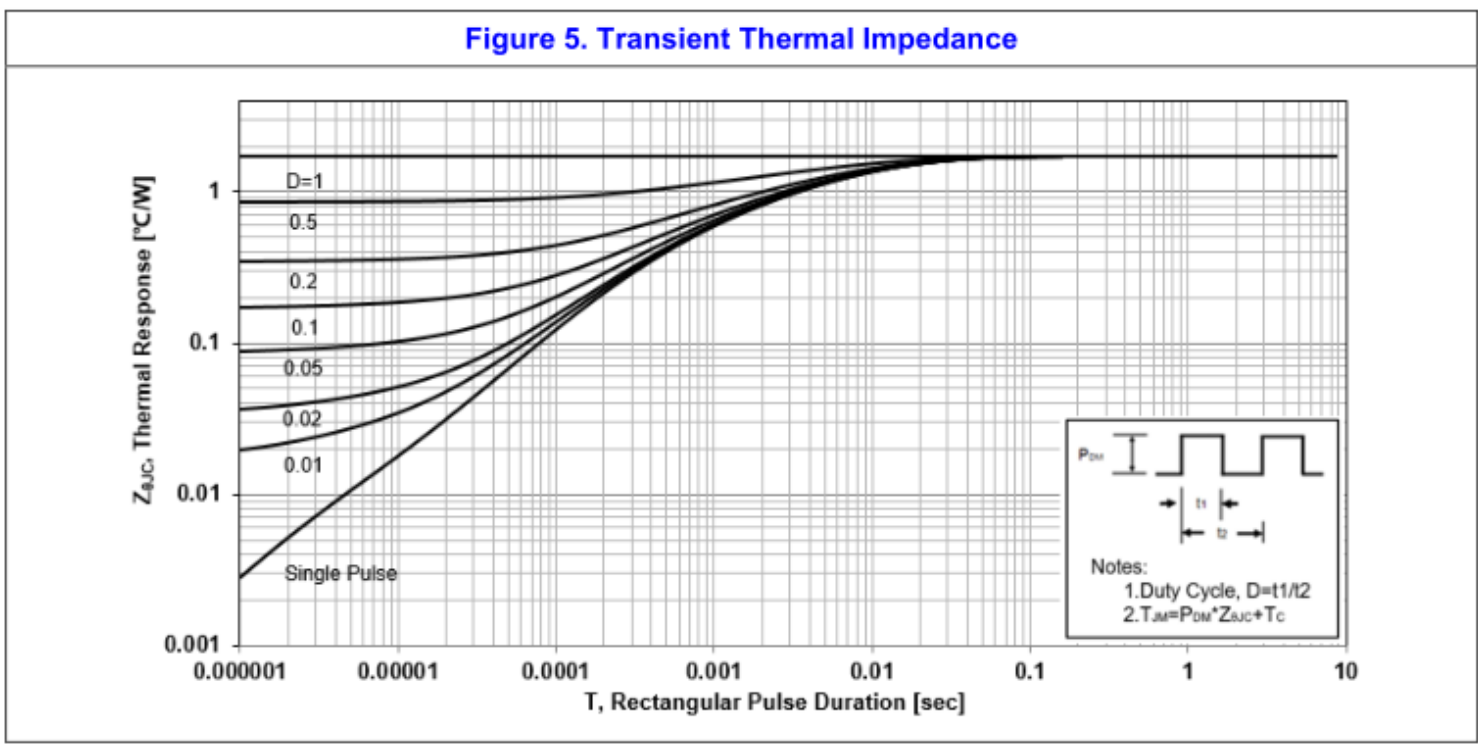
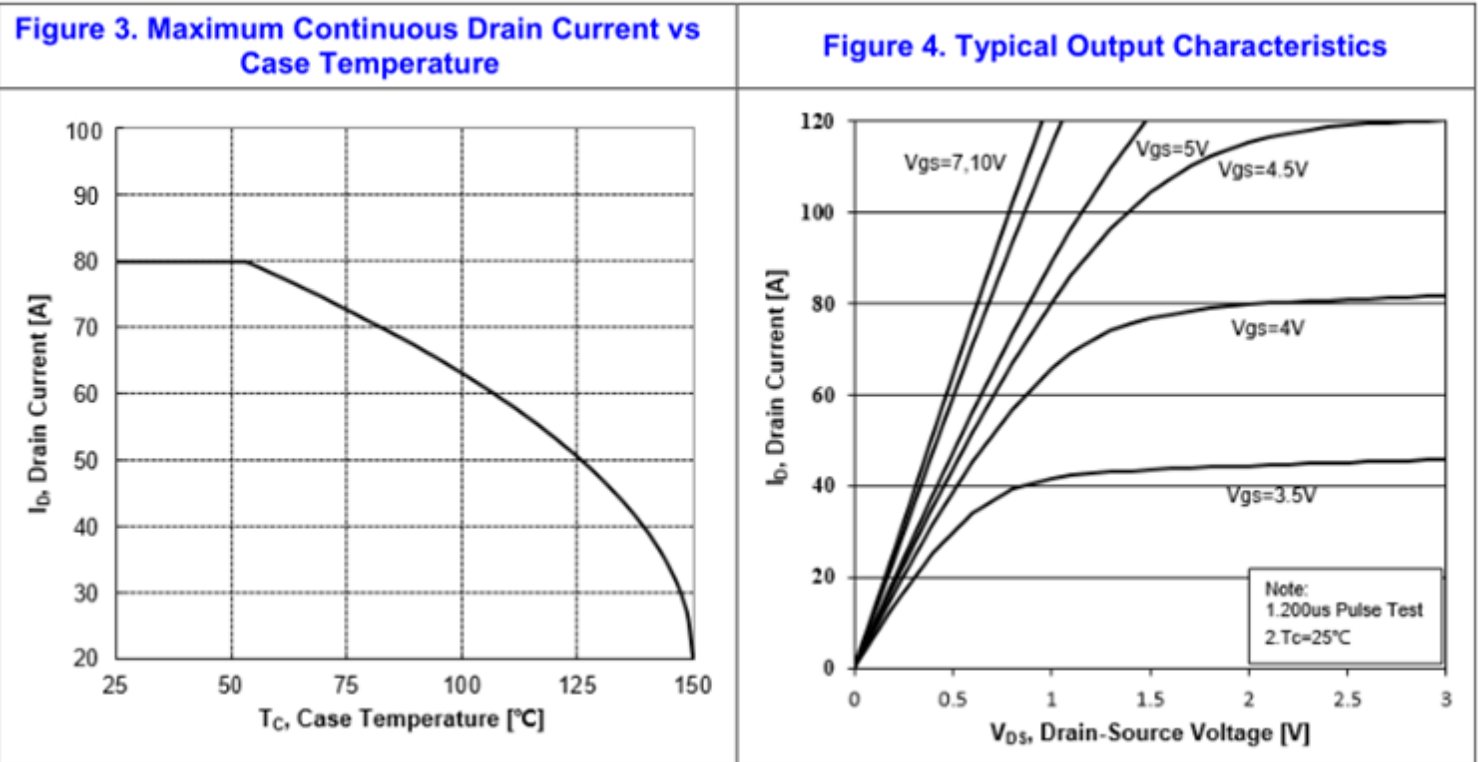
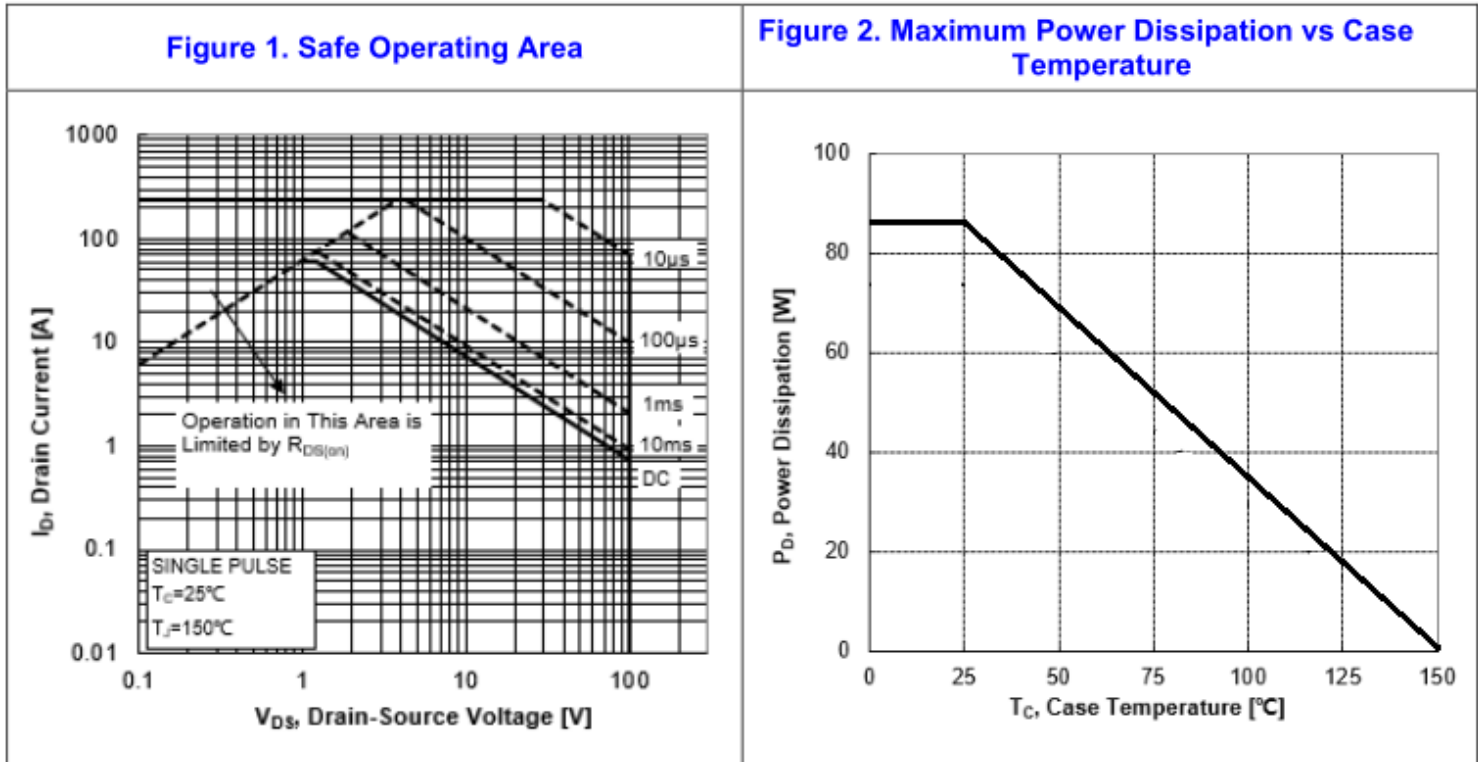
注释:

- 1: 脉冲宽度由最高结温限制
- 2: L=0.5mH, IAS=25A, VDD=50V, RG=25 Ω, 起始结温 TJ=25°C
- 3: ISD ≤60A, di/dt ≤100A/μs, VDD≤BVDS, 起始结温 TJ=25°C
- 4: 脉冲测试: 脉冲宽度 ≤300μs, 占空比≤2%
- 5: 基本与工作温度无关

Notes:

- 1: Pulse width limited by maximum junction temperature
- 2: L=0.5mH, IAS=25A, VDD=50V, RG=25 Ω, Starting TJ=25°C
- 3: ISD ≤60A, di/dt ≤100A/μs, VDD≤BVDS, Starting TJ=25°C
- 4: Pulse Test: Pulse Width ≤300μs, Duty Cycle≤2%
- 5: Essentially independent of operating temperature

特性曲线 Typical Characteristics



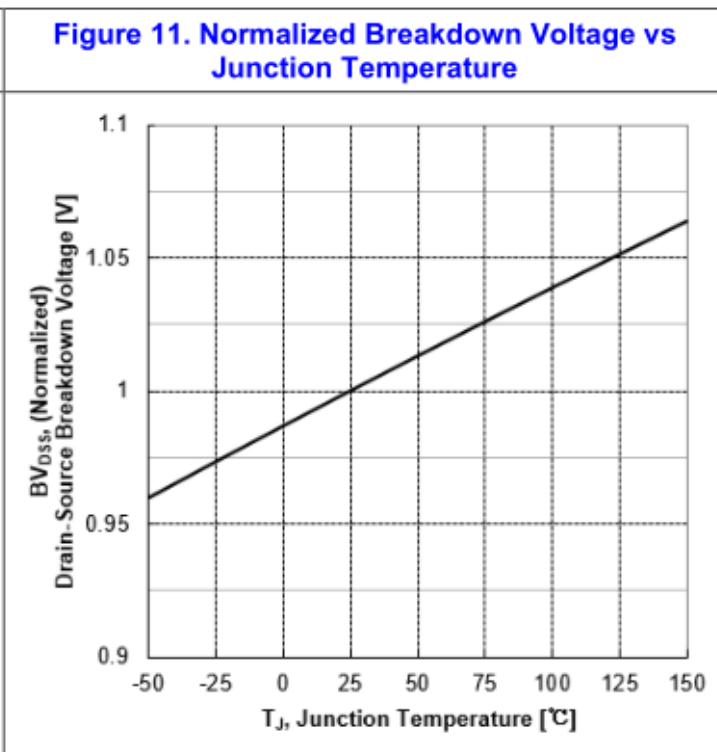
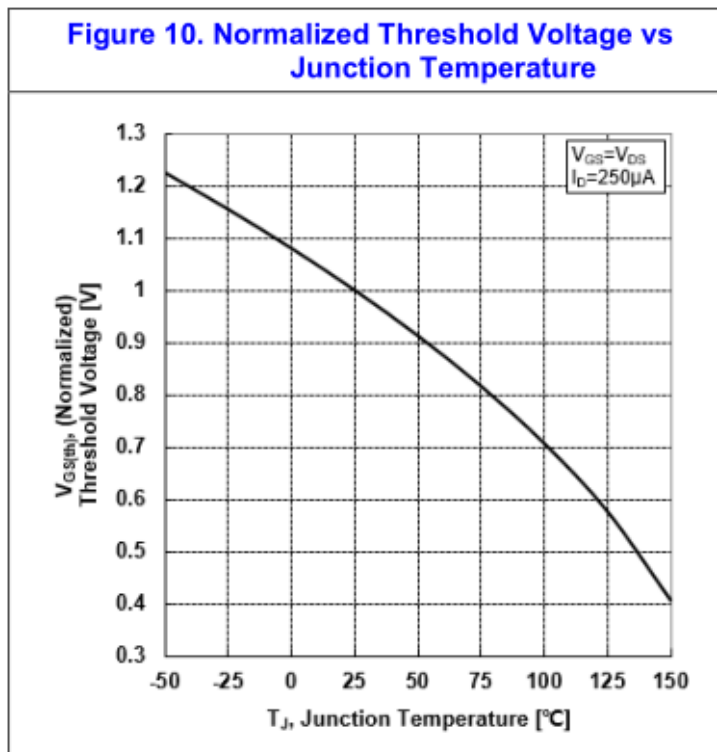
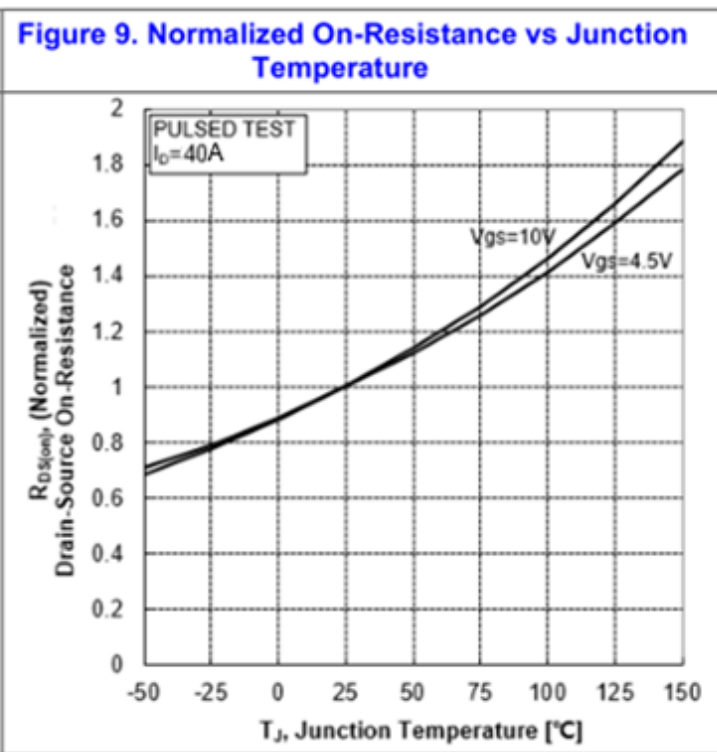
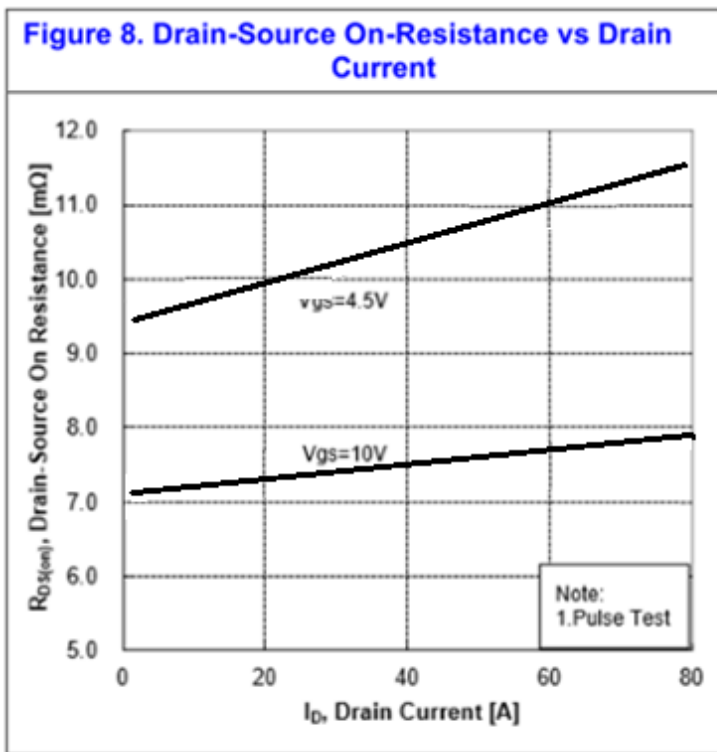
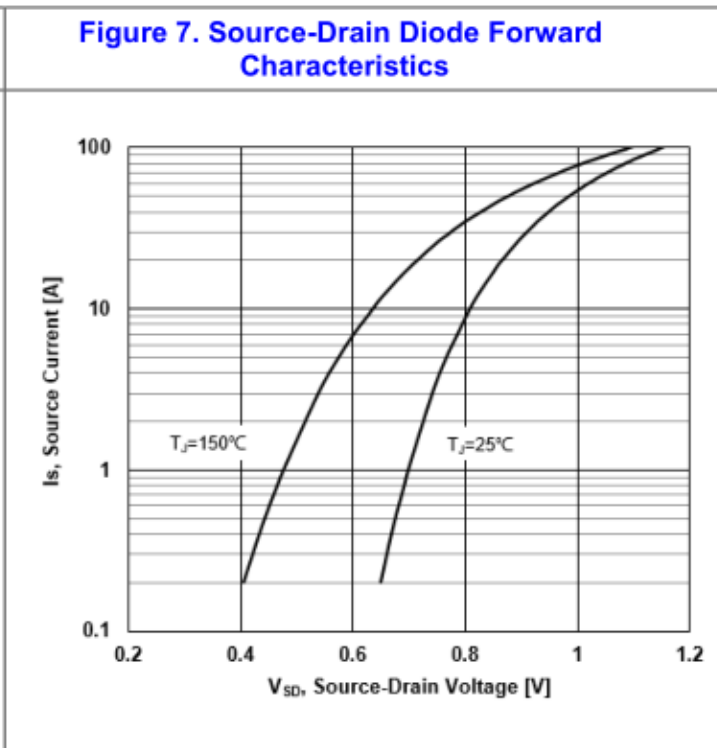
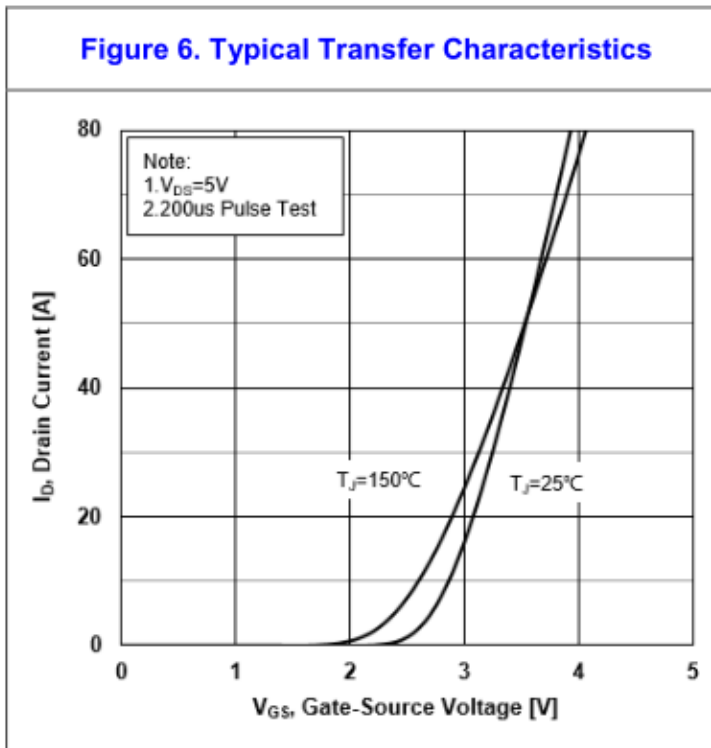


Figure 12. Capacitance Characteristics

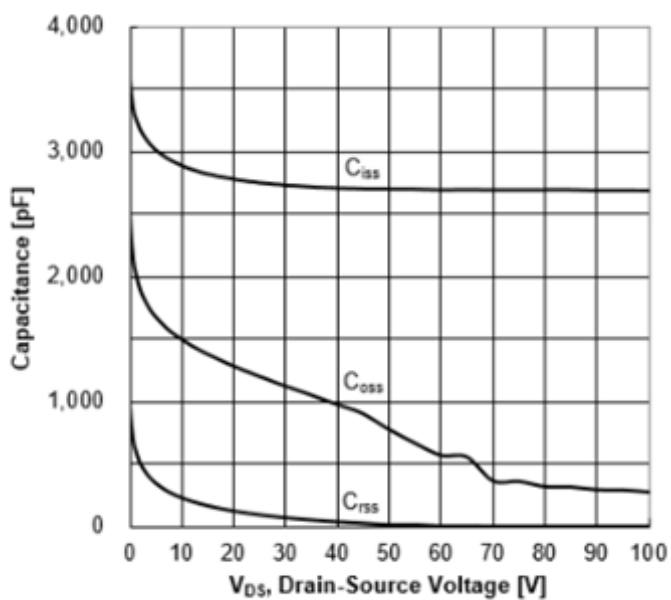
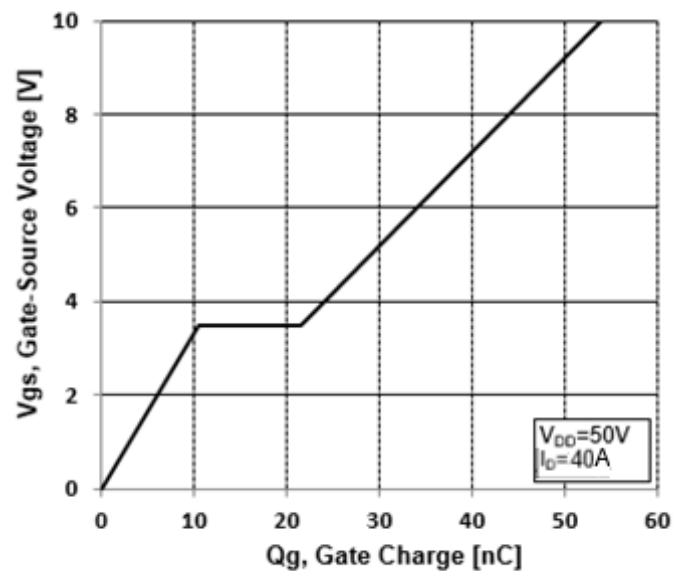
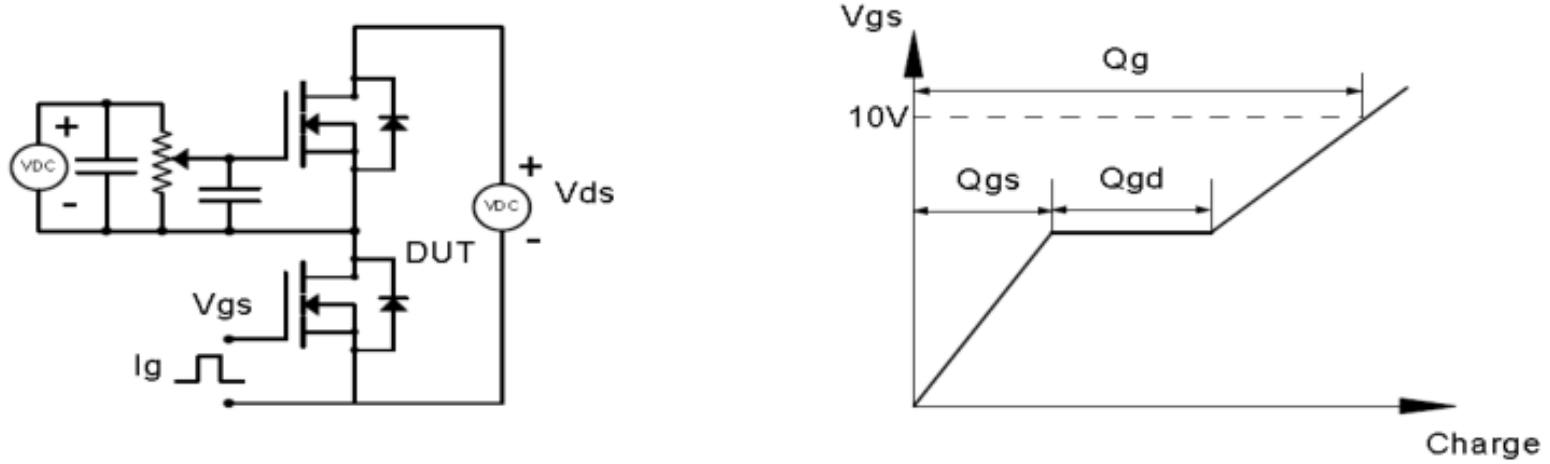


Figure 13. Typical Gate Charge vs Gate-Source Voltage

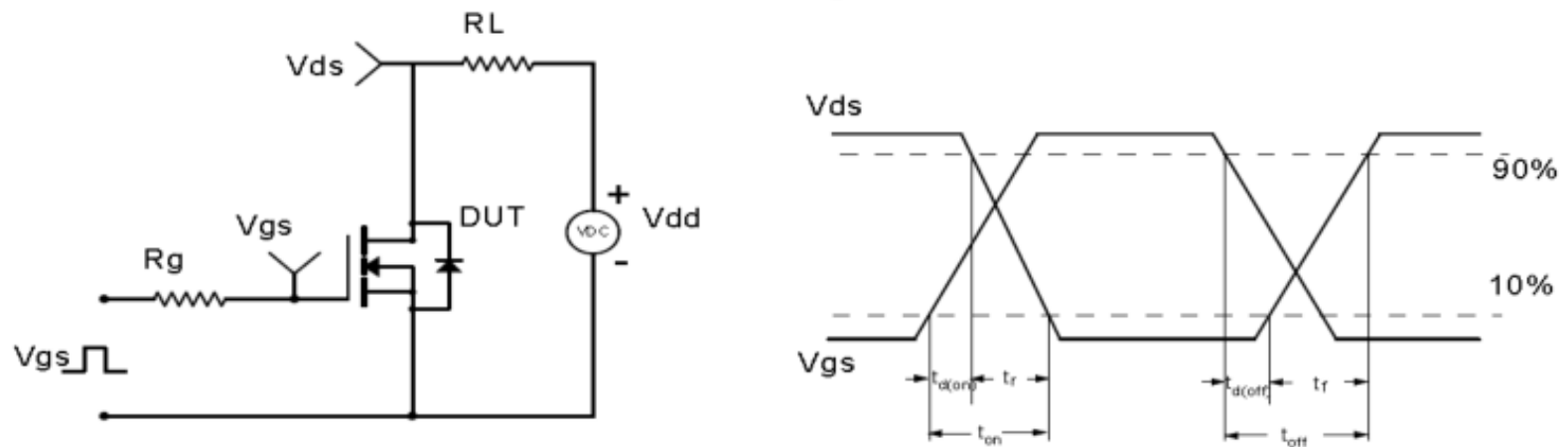


Test Circuit & Waveform

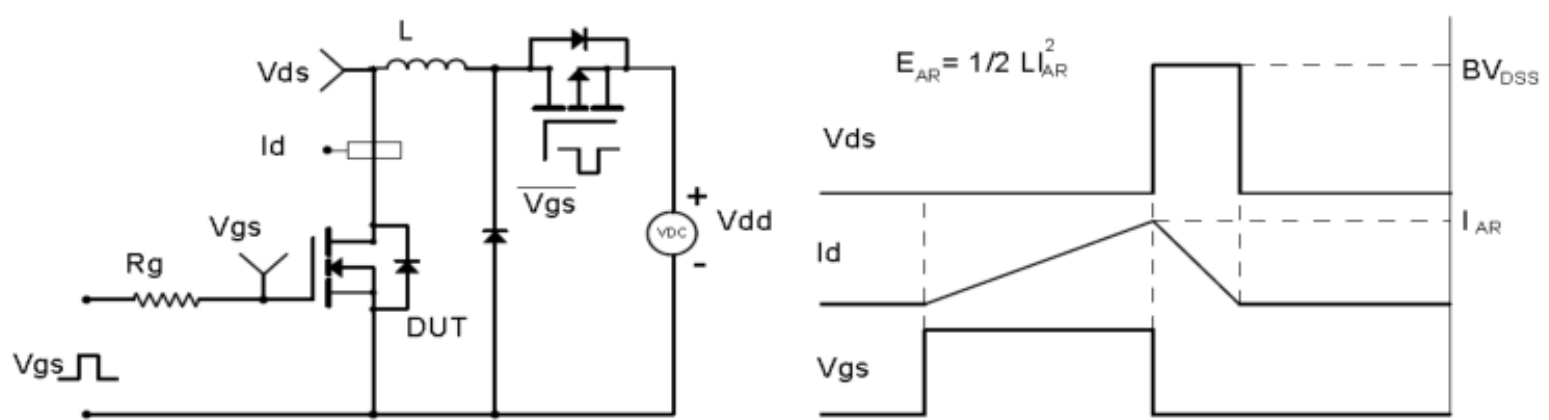
Gate Charge Test Circuit & Waveform



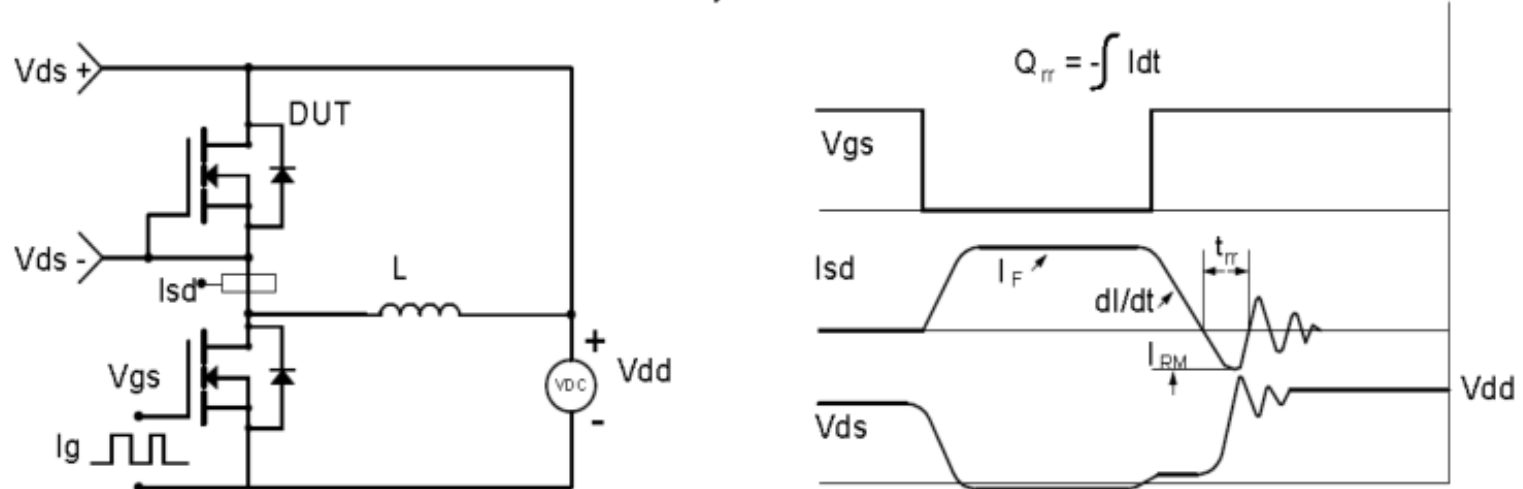
Resistive Switching Test Circuit & Waveforms



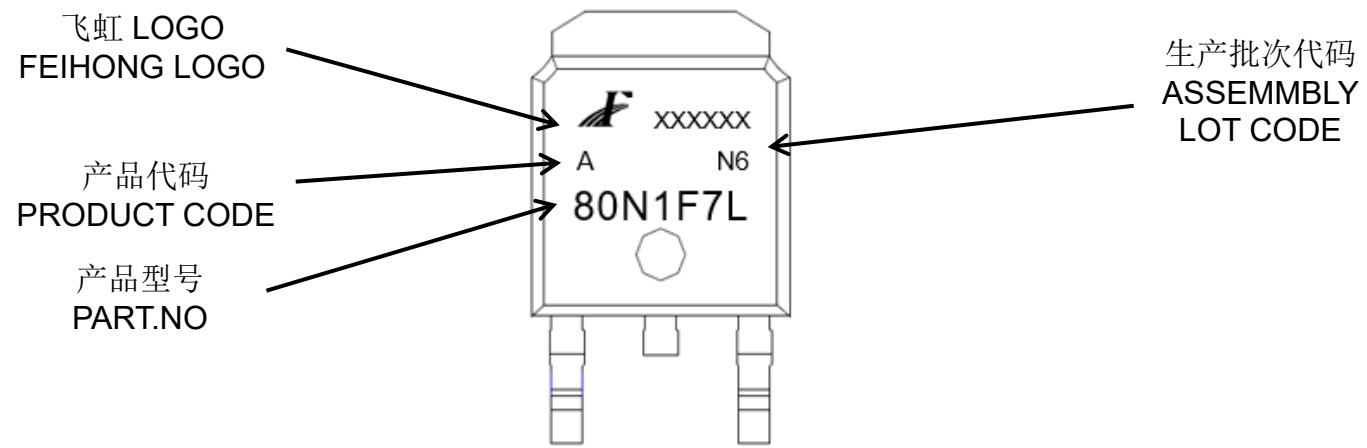
Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



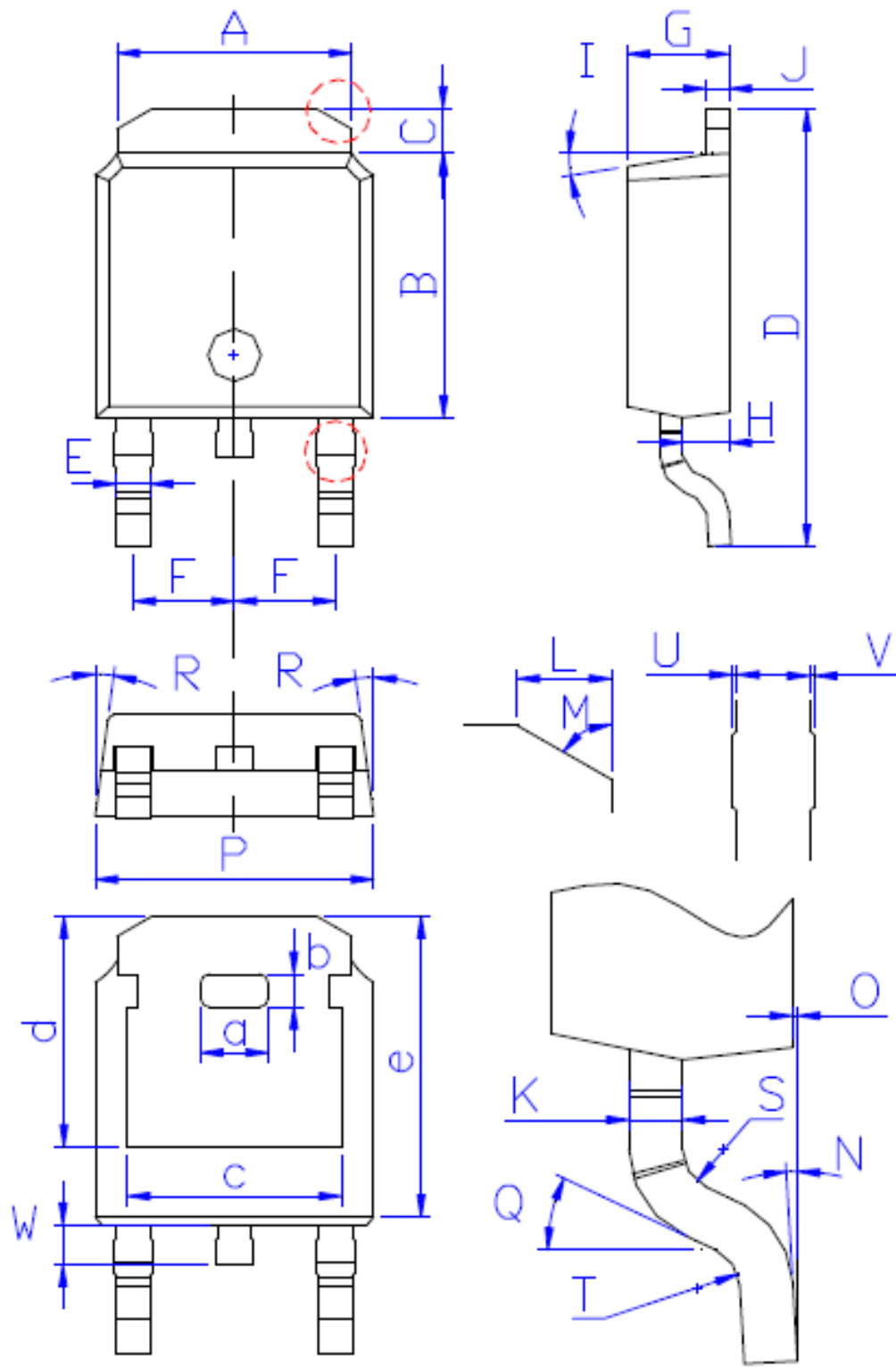
印记 Marking:



外形尺寸:

Package Dimension:

TO-252



DIM	MILLIMETERS
A	5.34 ± 0.30
B	6.00 ± 0.30
C	1.05 ± 0.30
D	9.95 ± 0.30
E	0.76 ± 0.15
F	2.28 ± 0.15
G	2.30 ± 0.30
H	1.06 ± 0.30
I	$(4-10)^\circ$
J	0.51 ± 0.15
K	0.52 ± 0.15
L	0.80 ± 0.30
M	60°
N	$(0-10)^\circ$
O	0.05 ± 0.05
P	6.60 ± 0.30
Q	25°
R	$(4-8.5)^\circ$
S	R0.40
T	R0.40
U	0.05 ± 0.05
V	0.05 ± 0.05
W	0.90 ± 0.30
a	1.80 ± 0.30
b	0.75 ± 0.30
c	4.85 ± 0.30
d	5.30 ± 0.30
e	6.90 ± 0.30

(Units: mm)